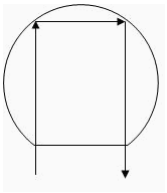
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 1 deg	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	Wafer Vendor
	5.0	Overall Thickness	527.80 +/- 7.50 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Bow	<60.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<60.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor - Topsil only
	12.0	Handle Orientation	{111} off 2.5 +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	350.00 +/- 5.00 µm	ADE, 100%
	14.0	Handle Doping Type	N	Wafer Vendor
	15.0	Handle Dopant	Arsenic	Wafer Vendor
	16.0	Handle Resistivity	<0.0025 Ohm cm	Wafer Vendor
	17.0	Backside Finish	Lapped and etched with no oxide & laser ID marking	Wafer Vendor
DeviceSilicon	20.0	Device Growth Method	FZ	Wafer Vendor - Topsil only
	21.0	Device Orientation	{111} off 3.5 +/- 1 degree	Wafer Vendor
	22.0	Nominal Thickness	177.80 +/- 2.50 µm	FTIR, 100% 9-Pt (note3)
	23.0	Distance to device silicon edge from wafer edge	<= 3mm	Typical by Process
	24.0	Device Doping Type	N	Wafer Vendor
	25.0	Device Dopant	Phosphorous	Wafer Vendor
	26.0	Device Resistivity	> 5000 Ohm-cm	Wafer Vendor
	28.0	Voids	0	Bright Light, 100% (note 2)
	29.0	Scratches	< 25mm total length	Bright Light, 100% (note 2)
	30.0	Haze	none	Bright Light, 100% (note 2)

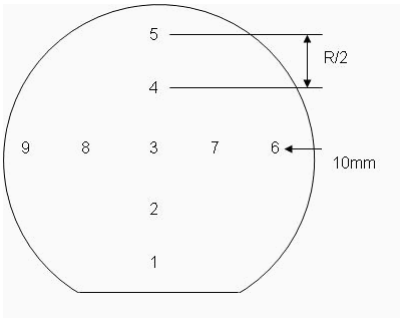
Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information